



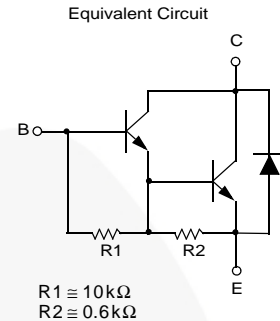
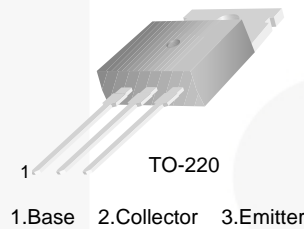
November 2014

# TIP110 / TIP111 / TIP112

## NPN Epitaxial Silicon Darlington Transistor

### Features

- Monolithic Construction with Built-in Base-Emitter Shunt Resistors
- Complementary to TIP115 / TIP116 / TIP117
- High DC Current Gain:  
 $h_{FE} = 1000 @ V_{CE} = 4 \text{ V}, I_C = 1 \text{ A}$  (Minimum)
- Low Collector-Emitter Saturation Voltage
- Industrial Use



### Ordering Information

| Part Number | Top Mark | Package                  | Packing Method |
|-------------|----------|--------------------------|----------------|
| TIP110      | TIP110   | TO-220 3L (Single Gauge) | Bulk           |
| TIP110TU    | TIP110   | TO-220 3L (Single Gauge) | Rail           |
| TIP111TU    | TIP111   | TO-220 3L (Single Gauge) | Rail           |
| TIP112      | TIP112   | TO-220 3L (Single Gauge) | Bulk           |
| TIP112TU    | TIP112   | TO-220 3L (Single Gauge) | Rail           |

### Absolute Maximum Ratings

Stresses exceeding the absolute maximum ratings may damage the device. The device may not function or be operable above the recommended operating conditions and stressing the parts to these levels is not recommended. In addition, extended exposure to stresses above the recommended operating conditions may affect device reliability. The absolute maximum ratings are stress ratings only. Values are at  $T_C = 25^\circ\text{C}$  unless otherwise noted.

| Symbol    | Parameter                 | Value      | Unit             |
|-----------|---------------------------|------------|------------------|
| $V_{CBO}$ | Collector-Base Voltage    | TIP110     | 60               |
|           |                           | TIP111     | 80               |
|           |                           | TIP112     | 100              |
| $V_{CEO}$ | Collector-Emitter Voltage | TIP110     | 60               |
|           |                           | TIP111     | 80               |
|           |                           | TIP112     | 100              |
| $V_{EBO}$ | Emitter-Base Voltage      | 5          | V                |
| $I_C$     | Collector Current (DC)    | 2          | A                |
| $I_{CP}$  | Collector Current (Pulse) | 4          | A                |
| $I_B$     | Base Current (DC)         | 50         | mA               |
| $T_J$     | Junction Temperature      | 150        | $^\circ\text{C}$ |
| $T_{STG}$ | Storage Temperature Range | -65 to 150 | $^\circ\text{C}$ |

TIP110 / TIP111 / TIP112 — NPN Epitaxial Silicon Darlington Transistor

## Thermal Characteristics

Values are at  $T_C = 25^\circ\text{C}$  unless otherwise noted.

| Symbol | Parameter  | Value | Unit |
|--------|--|-------|------|
| $P_C$  | Collector Dissipation ( $T_A = 25^\circ\text{C}$ ) | 2     | W    |
|        | Collector Dissipation ( $T_C = 25^\circ\text{C}$ ) | 50    |      |

## Electrical Characteristics<sup>(1)</sup>

Values are at  $T_C = 25^\circ\text{C}$  unless otherwise noted.

| Symbol        | Parameter                            | Conditions   | Min.                             | Max. | Unit |
|---------------|--------------------------------------|--|----------------------------------|------|------|
| $V_{CE(sus)}$ | Collector-Emitter Sustaining Voltage | TIP110   | $I_C = 30\text{ mA}, I_B = 0$    | 60   | V    |
|               |                                      | TIP111   |                                  | 80   |      |
|               |                                      | TIP112   |                                  | 100  |      |
| $I_{CEO}$     | Collector Cut-Off Current            | TIP110   | $V_{CE} = 30\text{ V}, I_B = 0$  | 2    | mA   |
|               |                                      | TIP111   | $V_{CE} = 40\text{ V}, I_B = 0$  | 2    |      |
|               |                                      | TIP112   | $V_{CE} = 50\text{ V}, I_B = 0$  | 2    |      |
| $I_{CBO}$     | Collector Cut-Off Current            | TIP110   | $V_{CB} = 60\text{ V}, I_E = 0$  | 1    | mA   |
|               |                                      | TIP111   | $V_{CB} = 80\text{ V}, I_E = 0$  | 1    |      |
|               |                                      | TIP112   | $V_{CB} = 100\text{ V}, I_E = 0$ | 1    |      |
| $I_{EBO}$     | Emitter Cut-Off Current              | $V_{EB} = 5\text{ V}, I_C = 0$                           |                                  | 2    | mA   |
| $h_{FE}$      | DC Current Gain                      | $V_{CE} = 4\text{ V}, I_C = 1\text{ A}$                  | 1000                             |      |      |
|               |                                      | $V_{CE} = 4\text{ V}, I_C = 2\text{ A}$                  | 500                              |      |      |
| $V_{CE(sat)}$ | Collector-Emitter Saturation Voltage | $I_C = 2\text{ A}, I_B = 8\text{ mA}$                    |                                  | 2.5  | V    |
| $V_{BE(on)}$  | Base-Emitter On Voltage              | $V_{CE} = 4\text{ V}, I_C = 2\text{ A}$                  |                                  | 2.8  | V    |
| $C_{ob}$      | Output Capacitance                   | $V_{CB} = 10\text{ V}, I_E = 0,$<br>$f = 0.1\text{ MHz}$ |                                  | 100  | pF   |

### Note:

1. Pulse test:  $p_w \leq 300\text{ }\mu\text{s}$ , duty cycle  $\leq 2\%$ .

## Typical Performance Characteristics

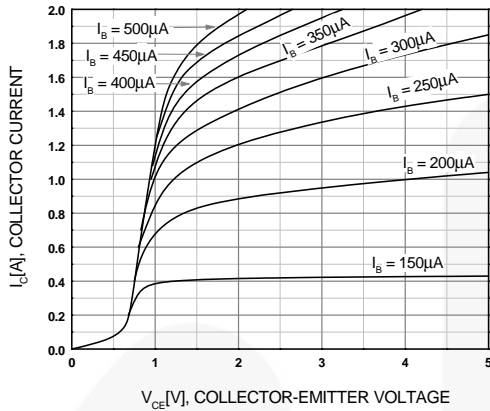


Figure 1. Static Characteristic

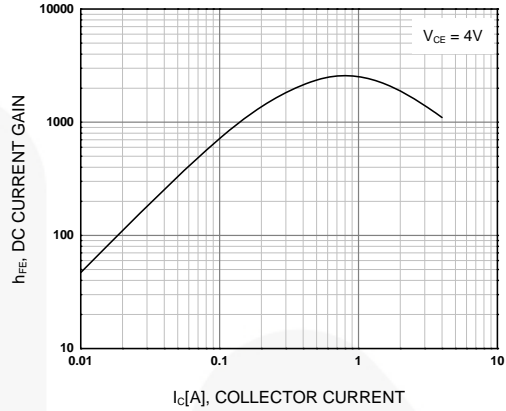


Figure 2. DC Current Gain

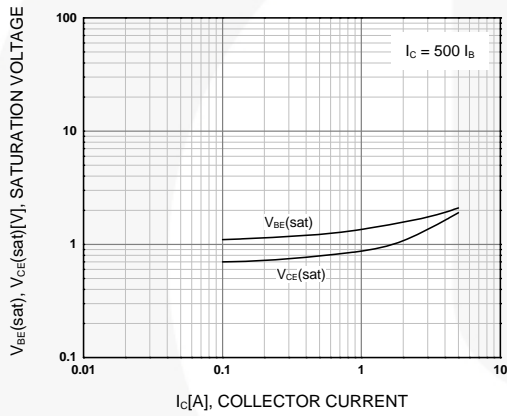


Figure 3. Base-Emitter Saturation Voltage and Collector-Emitter Saturation Voltage

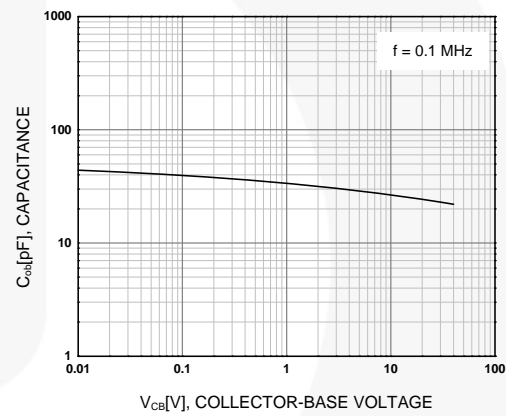


Figure 4. Collector Output Capacitance

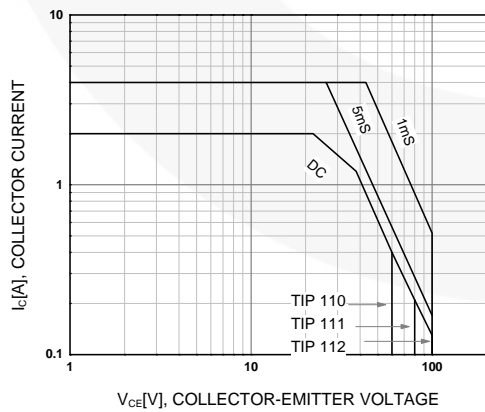


Figure 5. Safe Operating Area

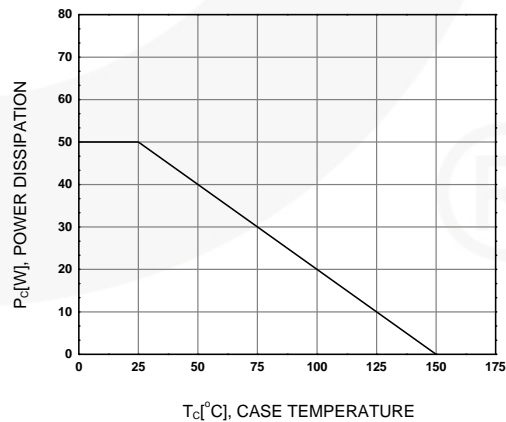


Figure 6. Power Derating

Physical Dimensions

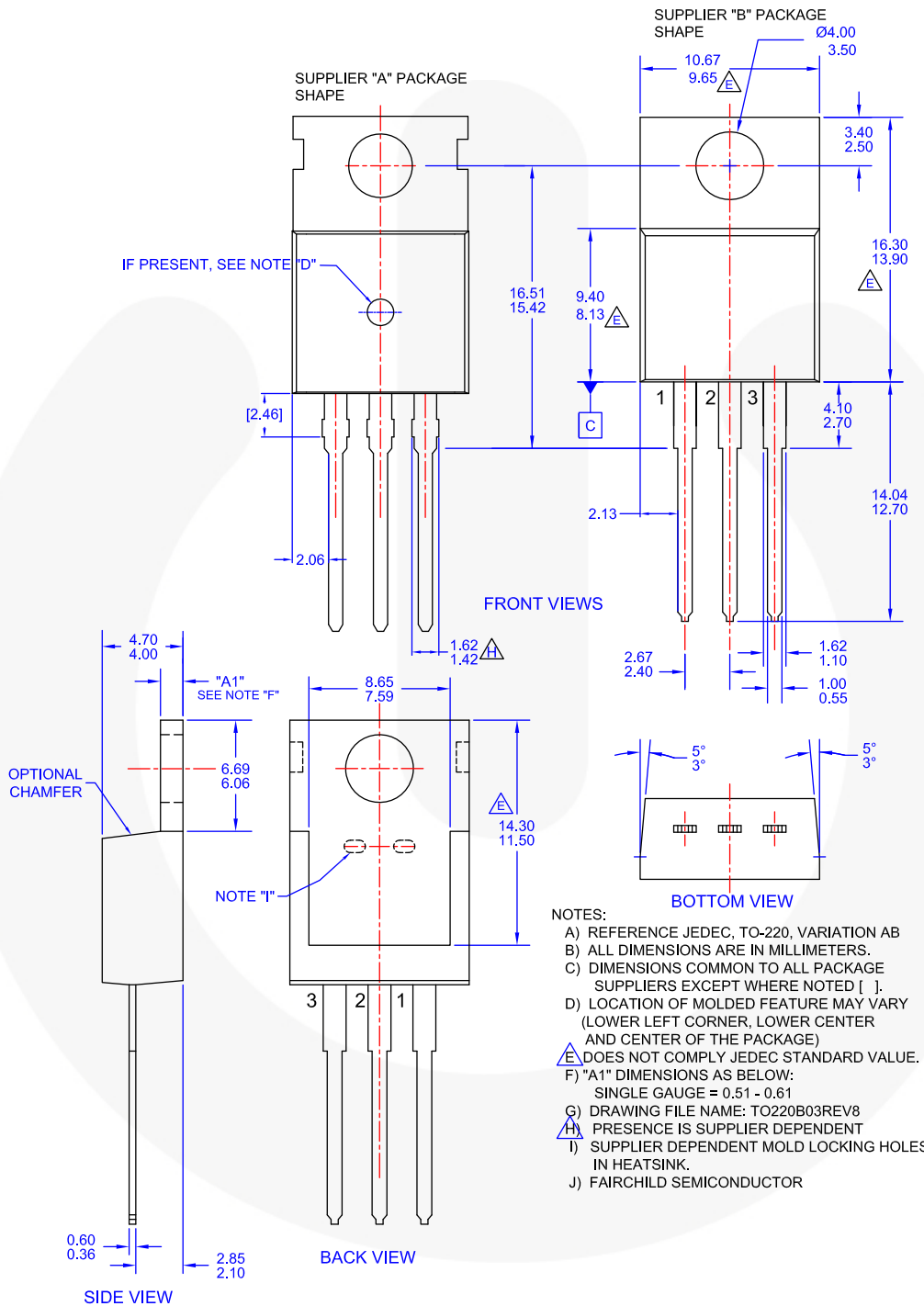







Figure 7. TO-220, MOLDED, 3LEAD, JEDEC VARIATION AB



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